

MJ21193 - PNP MJ21194 - NPN

Silicon Power Transistors

The MJ21193 (PNP) and MJ21194 (NPN) utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

Features

- Total Harmonic Distortion Characterized
- High DC Current Gain
- Excellent Gain Linearity
- High SOA
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	250	Vdc
Collector-Base Voltage	V_{CBO}	400	Vdc
Emitter-Base Voltage	V_{EBO}	5	Vdc
Collector-Emitter Voltage - 1.5 V	V_{CEX}	400	Vdc
Collector Current - Continuous	I_C	16	Adc
Collector Current - Peak (Note 1)	I_{CM}	30	Adc
Base Current - Continuous	I_B	5	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate Above 25°C	P_D	250 1.43	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 μs , Duty Cycle $\leq 10\%$. (continued)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	$^\circ\text{C}/\text{W}$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

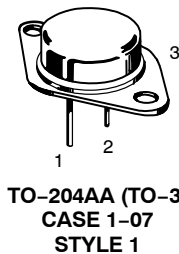
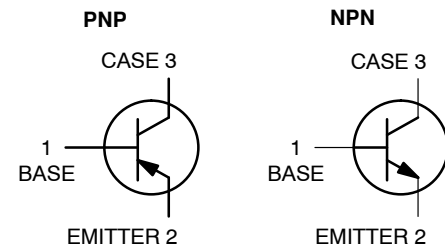


ON Semiconductor®

<http://onsemi.com>

16 AMP COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 250 WATTS

SCHEMATIC



MARKING DIAGRAM



MJ2119x = Device Code
x = 3 or 4

G = Pb-Free Package
A = Assembly Location
YY = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping†
MJ21193G	TO-3 (Pb-Free)	100 Units / Tray
MJ21194G	TO-3 (Pb-Free)	100 Units / Tray

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (I _C = 100 mA _{dc} , I _B = 0)	V _{CEO(sus)}	250	–	–	V _{dc}
Collector Cutoff Current (V _{CE} = 200 V _{dc} , I _B = 0)	I _{CEO}	–	–	100	μA _{dc}
Emitter Cutoff Current (V _{CE} = 5 V _{dc} , I _C = 0)	I _{EBO}	–	–	100	μA _{dc}
Collector Cutoff Current (V _{CE} = 250 V _{dc} , V _{BE(off)} = 1.5 V _{dc})	I _{CEX}	–	–	100	μA _{dc}

SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased (V _{CE} = 50 V _{dc} , t = 1 s (non-repetitive)) (V _{CE} = 80 V _{dc} , t = 1 s (non-repetitive))	I _{S/b}	5 2.5	– –	– –	A _{dc}
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ON CHARACTERISTICS

DC Current Gain (I _C = 8 A _{dc} , V _{CE} = 5 V _{dc}) (I _C = 16 A _{dc} , I _B = 5 A _{dc})	h _{FE}	25 8	– –	75	
Base–Emitter On Voltage (I _C = 8 A _{dc} , V _{CE} = 5 V _{dc})	V _{BE(on)}	–	–	2.2	V _{dc}
Collector–Emitter Saturation Voltage (I _C = 8 A _{dc} , I _B = 0.8 A _{dc}) (I _C = 16 A _{dc} , I _B = 3.2 A _{dc})	V _{CE(sat)}	– –	– –	1.4 4	V _{dc}

DYNAMIC CHARACTERISTICS

Total Harmonic Distortion at the Output V _{RMS} = 28.3 V, f = 1 kHz, P _{LOAD} = 100 W _{RMS} h _{FE} unmatched (Matched pair h _{FE} = 50 @ 5 A/5 V) h _{FE} matched	T _{HD}	– –	0.8 0.08	– –	% %
Current Gain Bandwidth Product (I _C = 1 A _{dc} , V _{CE} = 10 V _{dc} , f _{test} = 1 MHz)	f _T	4	–	–	MHz
Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f _{test} = 1 MHz)	C _{ob}	–	–	500	pF

NOTE: Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2%

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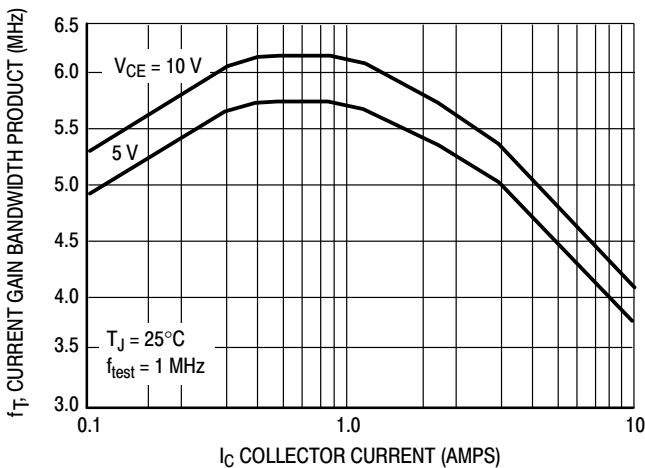


Figure 1. Typical Current Gain Bandwidth Product

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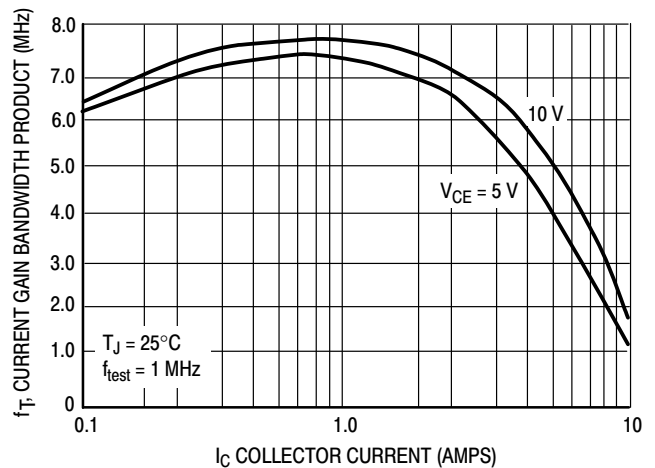


Figure 2. Typical Current Gain Bandwidth Product

TYPICAL CHARACTERISTICS

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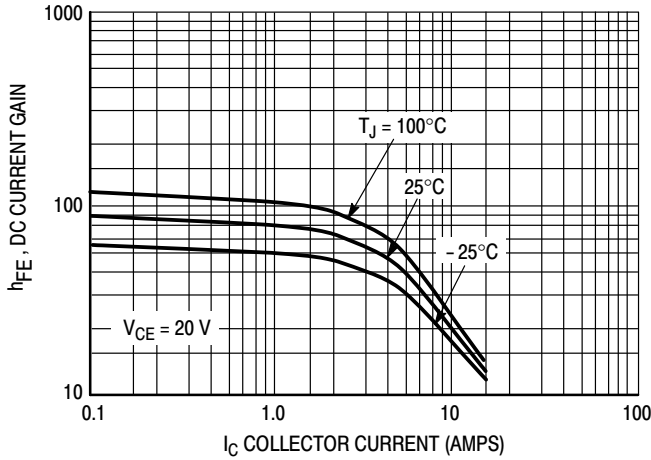


Figure 3. DC Current Gain, $V_{CE} = 20\text{ V}$

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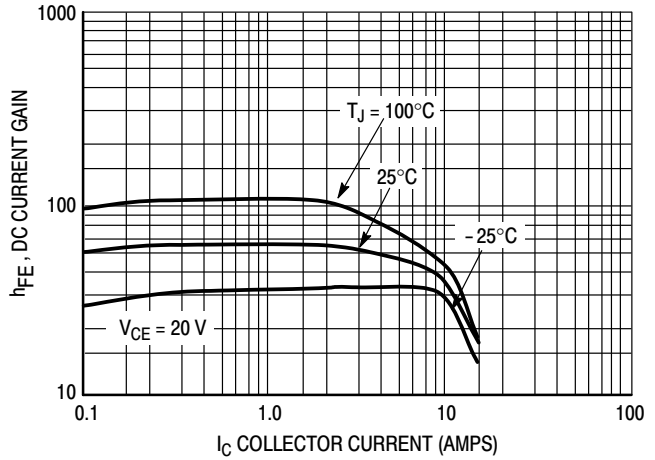


Figure 4. DC Current Gain, $V_{CE} = 20\text{ V}$

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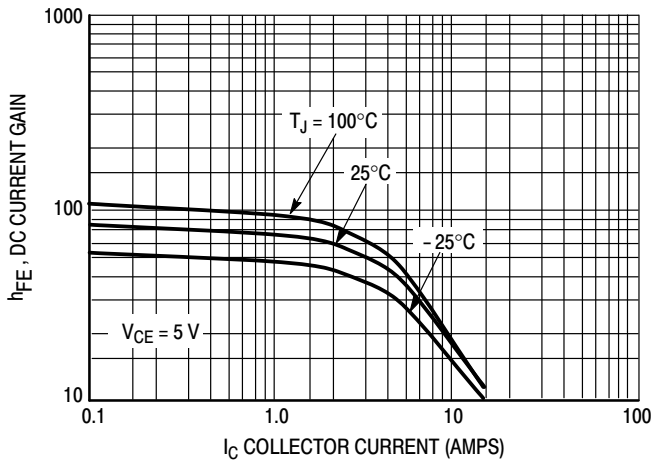


Figure 5. DC Current Gain, $V_{CE} = 5\text{ V}$

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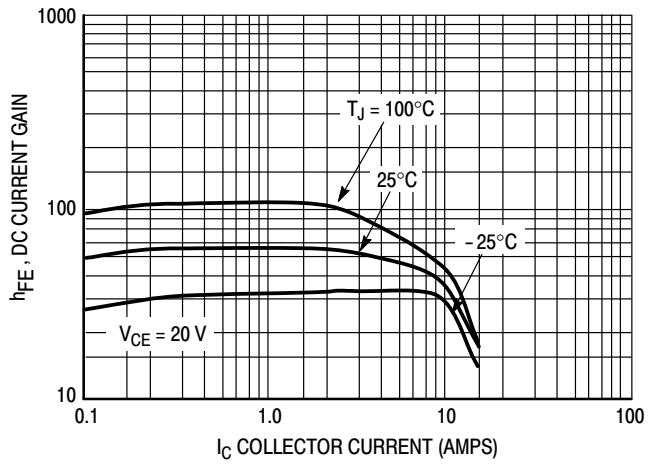


Figure 6. DC Current Gain, $V_{CE} = 5\text{ V}$

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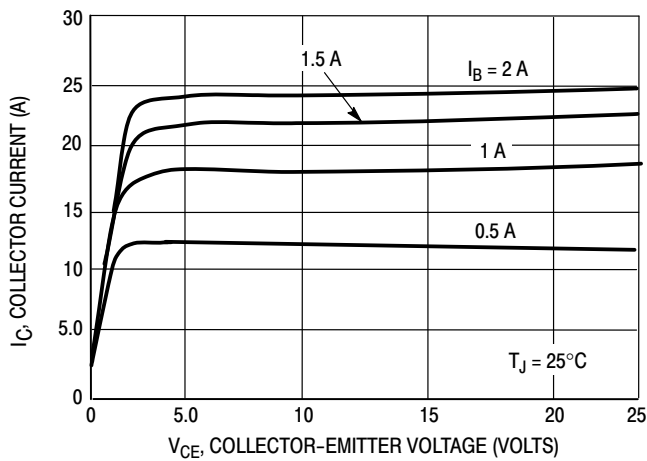


Figure 7. Typical Output Characteristics

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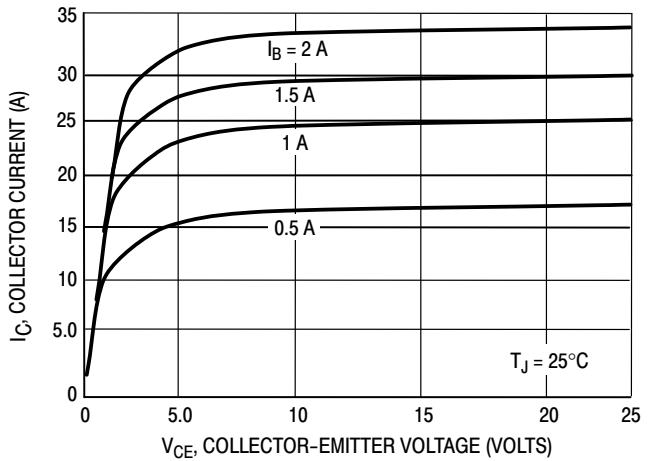


Figure 8. Typical Output Characteristics

TYPICAL CHARACTERISTICS

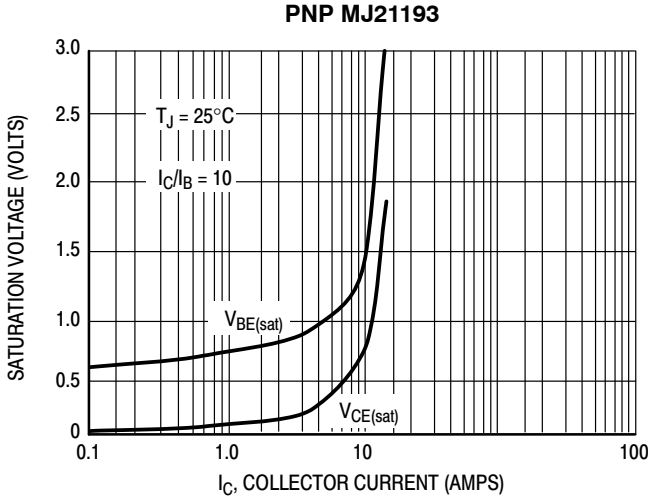


Figure 9. Typical Saturation Voltages

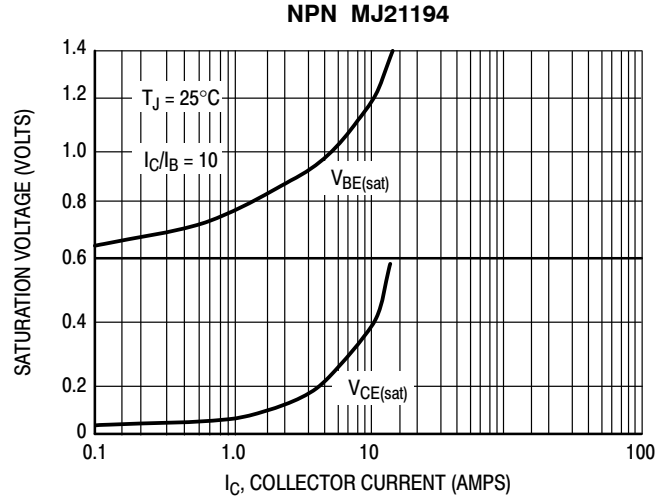


Figure 10. Typical Saturation Voltages

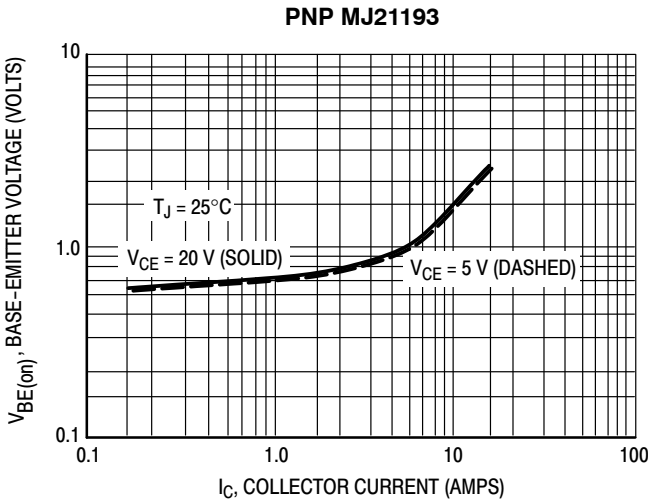


Figure 11. Typical Base-Emitter Voltage

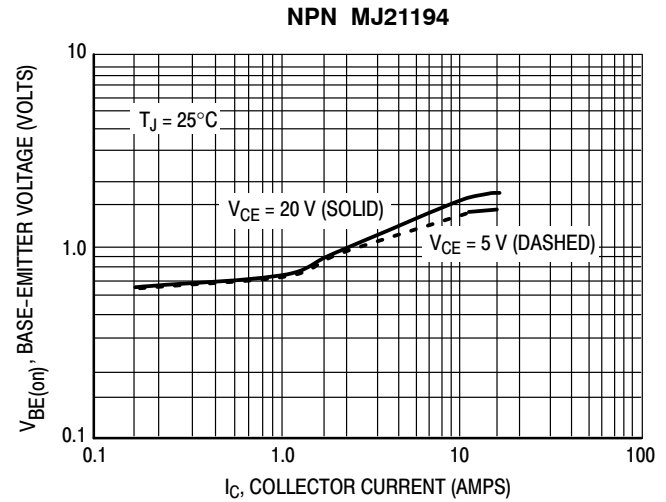


Figure 12. Typical Base-Emitter Voltage

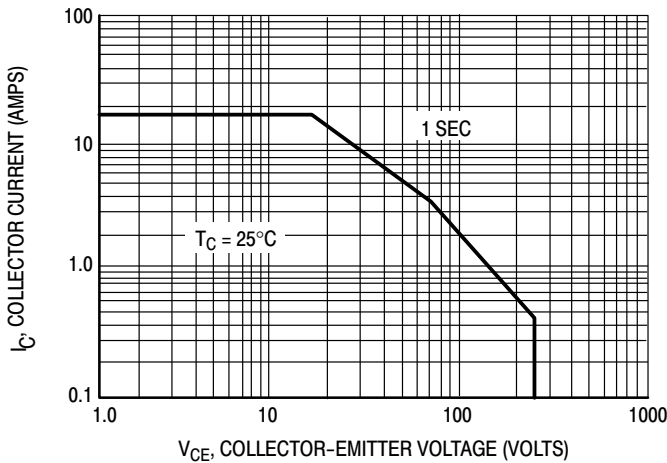


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)} = 200^\circ\text{C}$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

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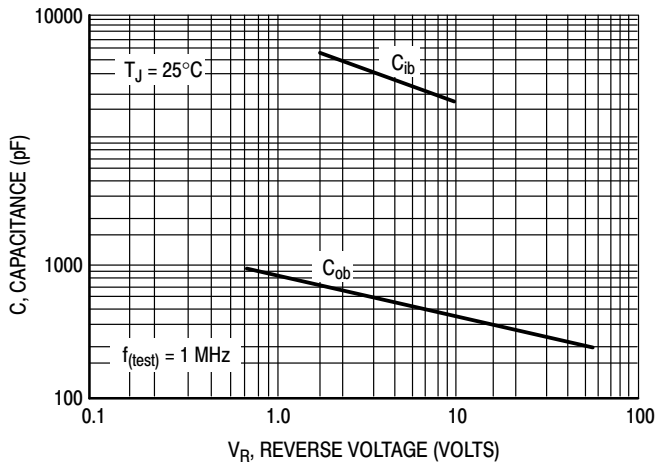


Figure 14. MJ21193 Typical Capacitance

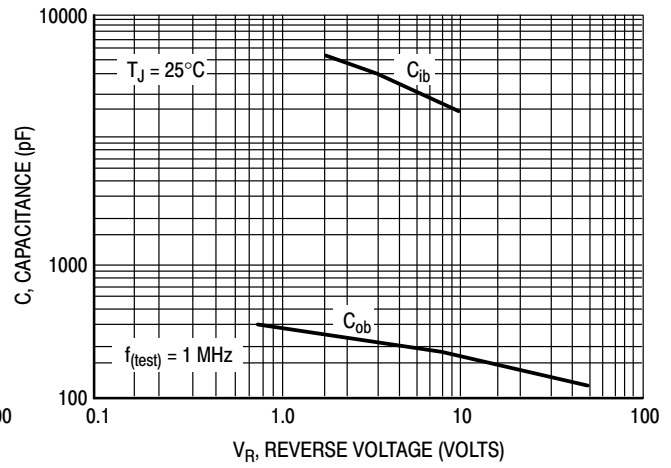


Figure 15. MJ21194 Typical Capacitance

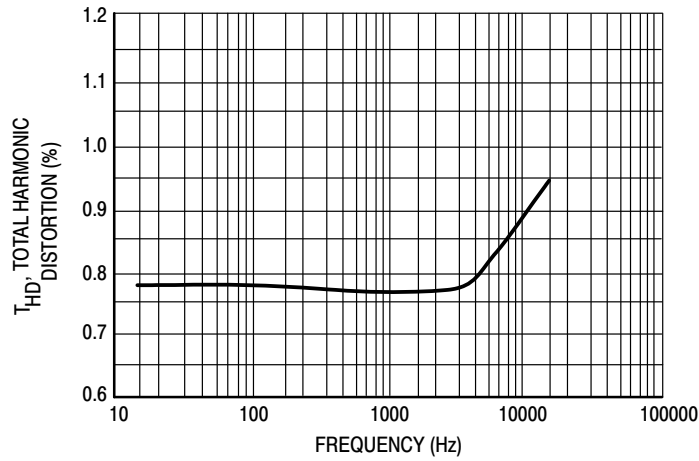


Figure 16. Typical Total Harmonic Distortion

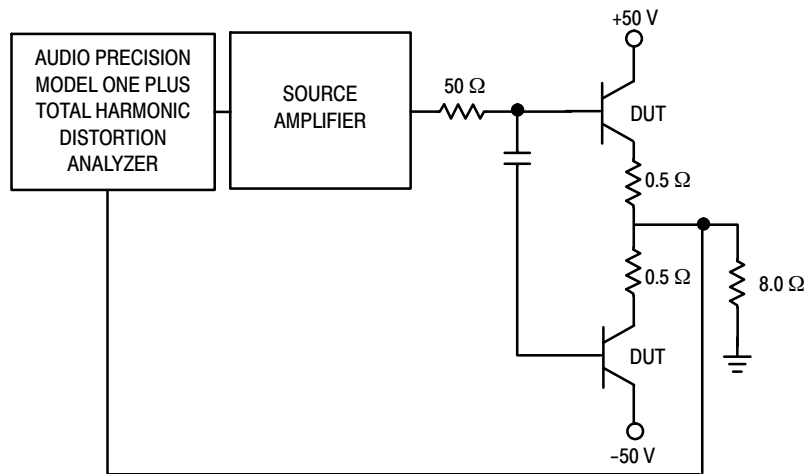


Figure 17. Total Harmonic Distortion Test Circuit

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